Triacs

Silicon Bidirectional Thyristors

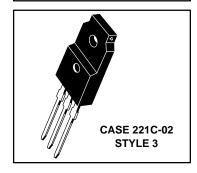
... designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC320FP Series) or Four Modes (MAC320AFP Series)



MAC320FP Series MAC320AFP Series

ISOLATED TRIACS THYRISTORS 20 AMPERES RMS 200 thru 800 VOLTS



MAXIMUM RATINGS (T_C = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (T _J = -40 to +125°C, 1/2 Sine Wave 50 to 60 Hz, Gate Open)	VDRM		Volts
MAC320-4FP, MAC320A4FP MAC320-6FP, MAC320A6FP MAC320-8FP, MAC320A8FP MAC320-10FP, MAC320A10FP		200 400 600 800	
Peak Gate Voltage	Vgм	10	Volts
On-State RMS Current (T _C = +75°C, Full Cycle Sine Wave 50 to 60 Hz) ⁽²⁾	lT(RMS)	20	Amps
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, T _C = +75°C, preceded and followed by rated current)	ITSM	150	Amps
Peak Gate Power (T _C = +75°C, Pulse Width = 2 μs)	P _{GM}	20	Watts
Average Gate Power (T _C = +75°C, t = 8.3 ms)	P _{G(AV)}	0.5	Watt
Peak Gate Current	I _{GM}	2	Amps
RMS Isolation Voltage (T _A = 25°C, Relative Humidity ≤ 20%)	V(ISO)	1500	Volts
Operating Junction Temperature	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.8	°C/W
Thermal Resistance, Case to Sink	R ₀ CS	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W

- 1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- 2. The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current $(V_D = Rated \ V_{DRM}, \ Gate \ Open)$ $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	IDRM	_	_	10 2	μA mA
Peak On-State Voltage (Either Direction) (I _{TM} = 28 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle ≤ 2%)	Vтм	_	1.4	1.7	Volts
Peak Gate Trigger Current (Main Terminal Voltage = 12 Vdc, R_L = 100 Ohms Minimum Gate Pulse Width = 2 μ s) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(-) "A" SUFFIX ONLY	I _{GT}	_ _ _ _	_ _ _ _	50 50 50 75	mA
Peak Gate Trigger Voltage (Main Terminal Voltage = 12 Vdc, R _L = 100 Ohms Minimum Gate Pulse Width = 2 μ s) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY (Main Terminal Voltage = Rated V _{DRM} , R _L = 10 , T _J = +110°C) MT2(+), G(+); MT2(+), G(-) MT2(-), G(-); MT2(-), G(-); MT2(-), G(-); MT2(-), G(-)	VGT		0.9 0.9 1.1 1.4	2 2 2 2.5 —	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 200 mA)	lн	_	6	40	mA
Turn-On Time (V_D = Rated V_{DRM} , I_{TM} = 28 A, I_{GT} = 120 mA, Rise Time = 0.1 μ s, Pulse Width = 2 μ s)	^t gt	_	1.5	10	μs
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM} , I_{TM} = 28 A, Commutating di/dt = 10 A/ms, Gate Unenergized, T_C = +75°C)	dv/dt(c)		5	_	V/µs

TYPICAL CHARACTERISTICS

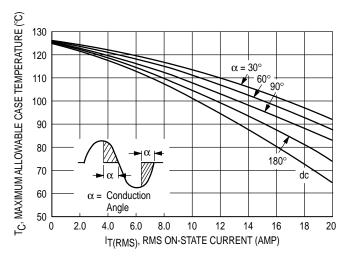


Figure 1. RMS Current Derating

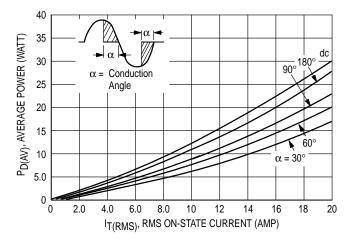


Figure 2. On-State Power Dissipation

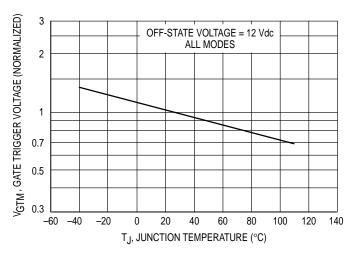


Figure 3. Typical Gate Trigger Voltage

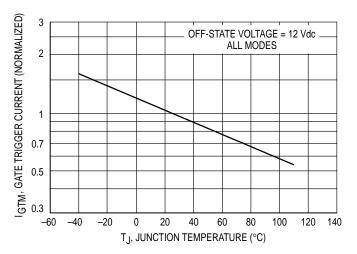


Figure 4. Typical Gate Trigger Current

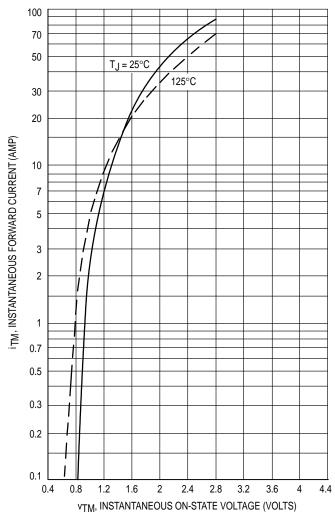
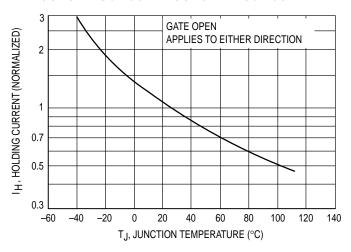


Figure 5. Maximum On-State Characteristics



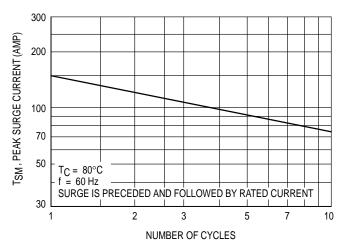


Figure 6. Typical Holding Current

Figure 7. Maximum Nonrepetitive Surge Current

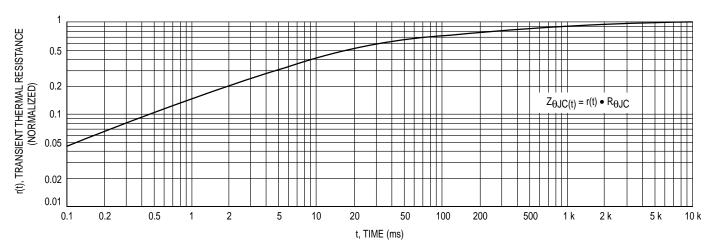
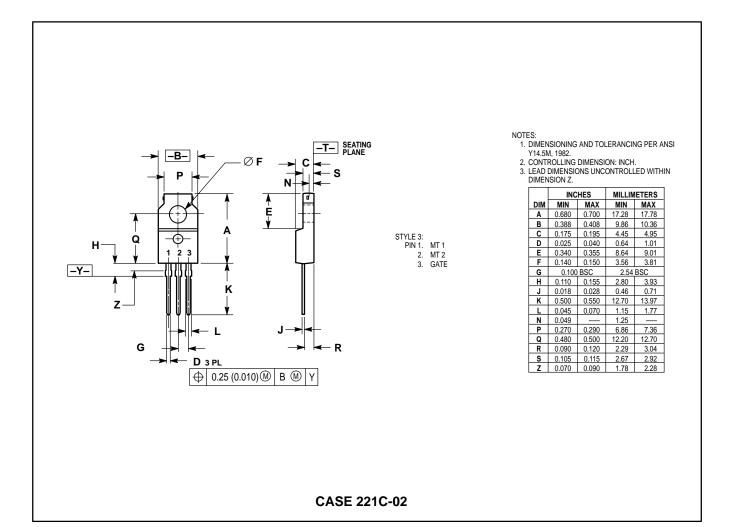


Figure 8. Thermal Response

PACKAGE DIMENSIONS



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MAC320FP/D